

ABSTRACT:

A semiconductor arrangement including:

- a substrate having a substrate layer (13) with an upper and lower surface, the substrate layer (13) being of a first conductivity type;
- a first buried layer (12) in the substrate, extending along said lower surface below a first portion of said upper surface of said substrate layer (13), and a second buried layer (12) in the substrate, extending along said lower surface below a second portion of said upper surface of said substrate layer (13);
- a first diffusion (26) in said first portion of said substrate layer (13), being of a second conductivity type opposite to said first conductivity type and having a first distance to said first buried layer (12) for defining a first breakdown voltage between said first diffusion (26) and said first buried layer (12);
- a second diffusion (45) in said second portion of said substrate layer (13), being of said second conductivity type and having a second distance to said second buried layer (12) for defining a second breakdown voltage between said second diffusion (45) and said second buried layer (12);

said first distance being larger than said second distance such that said first breakdown voltage is larger than said second breakdown voltage.

Fig.4a

BEST AVAILABLE COPY

09/972576-100501